



Product Change Notification



Product Group: DIODES / June 29, 2015 / PCN-DD-021-2015 Rev 0

Change wafer diameter on IGBT die used in modules

DESCRIPTION OF CHANGE: The silicon Wafer diameter used as raw material for Diodes will change from 6 inches (150mm) to 8 inches (200mm). IGBT die will have resistor in series to the gate already embedded in the die and therefore the switching characteristics of the device will slightly change. To facilitate comprehension of device performances in end user application, the data sheet will be updated.

CLASSIFICATION OF CHANGE: Wafer/Chip/Pellet Layout/Design

REASON FOR CHANGE: Continuous improvement

EXPECTED INFLUENCE ON QUALITY/RELIABILITY/PERFORMANCE:
There will be no effect on the quality, reliability and/or performances.

PRODUCT CATEGORY: Modules

PART NUMBERS/SERIES/FAMILIES AFFECTED:

VS-GT175DA120U

VISHAY BRAND(s): Vishay Semiconductors

TIME SCHEDULE: Starting from September 7, 2015 Vishay will gradually start to implement the above change.

SAMPLE AVAILABILITY: Samples available upon request

PRODUCT IDENTIFICATION: N/A

QUALIFICATION DATA: Qualification report available upon request

This PCN is considered approved, without further notification, unless we receive specific customer concerns before August 31, 2015 or as specified by contract.

ISSUED BY: Fabio Modaro, Product Marketing Manager
e-mail: Fabio.Modaro@Vishay.com

For further information, please contact your regional Vishay office.

CONTACT INFORMATION:

The Americas

Vishay Semiconductors.
150 Motor Parkway, Suite, 101E
Hauppauge, NY 11788 USA
Phone : 631 300 3816
Fax: 631 300 3843
Diodes-Americas@vishay.com

Europe

Vishay Semiconductors
Theresienstrasse 2
D-74072 Heilbronn, Germany
Phone: + 49 7131 67 3364 (3365)
Fax: + 49 7131 67 2938
Diodes-Europe@vishay.com

Asia

Vishay Semiconductors
15D, Sun Tong Infoport
55 Huai Hai West Road,
Shanghai, China
Phone: + 86 138 1787 2112
Fax: + 86 21 5258 7979
Diodes-Asia@vishay.com